

LAB REPORT: 7

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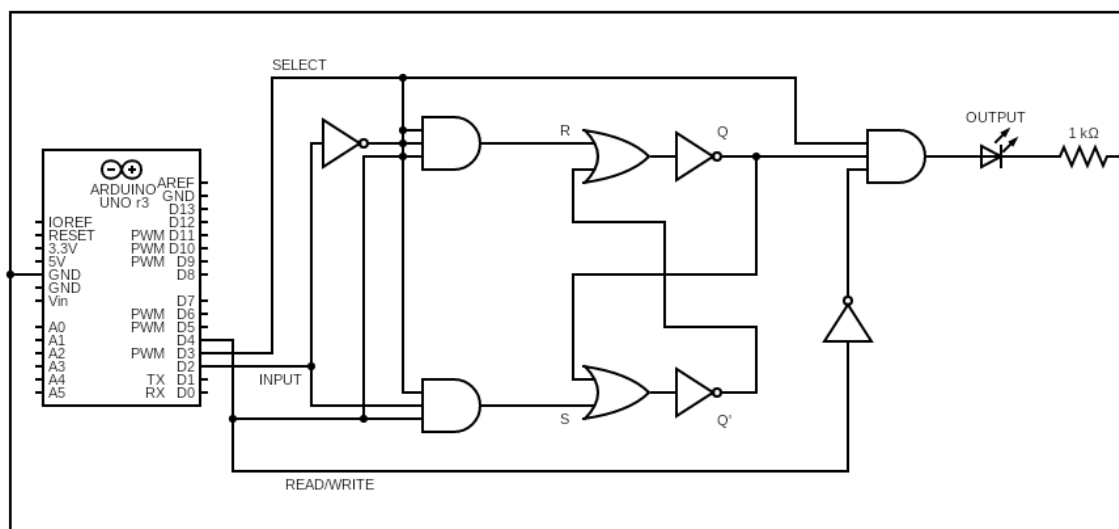
Aim/Objective of the experiment:

To implement and verify the operation of a binary cell for RAM based on RS flip-flop

Electronic components used:

Arduino Uno R3, 3 breadboards, 1 kilo ohm resistor, LED, 3 hex inverter ICs(74HC04), two 3-input AND gate ICs(74HC11), quad OR gate IC(74HC32), pushbutton, wires

Reference Circuit:



Procedure:

1. The binary memory cell is designed in accordance with the circuit diagram above.
2. The Select, Read/Write and Input values are taken as inputs from Arduino.
3. Appropriate code is written on Arduino.
4. The outputs are noted for a sequence of inputs.

The code:

```
int s,rw,i;

void setup()
{
    pinMode(3,OUTPUT);
    pinMode(4,OUTPUT);
    pinMode(2,OUTPUT);

    Serial.begin(9600);
}

void loop()
{
    if(Serial.available()>0)
    {
        s=Serial.read();
        s=s-'0';
        digitalWrite(3,s);
    }

    if(Serial.available()>0)
    {
        rw=Serial.read();
        rw=rw-'0';
        digitalWrite(4,rw);
    }

    if(Serial.available()>0)
    {
        i=Serial.read();
        i=i-'0';
    }
}
```

```

        digitalWrite(2,i);
    }

    delay(100);
}

```

Conclusion:

The output values are tabulated for 16 input stream:

Select (S)	Read/Write (RW)	Input (I)	OUTPUT
1	1	1	0
1	0	0	1
1	0	1	1
1	1	0	0
1	0	0	0
1	0	1	0
1	1	1	0
1	0	0	1
1	0	1	1
0	0	0	0
0	1	0	0
0	0	1	0
0	1	1	0
1	1	1	0
1	0	0	1
1	0	1	1

So, the operation of the memory cell is verified.

TinderCAD simulation:

<https://www.tinkercad.com/things/7mZxoTUhl9i-arghya-lab-7/>
